Liann-Be Chang

List of Publications by Year
in descending order

57	667	687363	610901
papers	citations	13	24
		h-index	g-index

58	58	58	877
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	A Surface Acoustic Wave Sensor with a Microfluidic Channel for Detecting C-Reactive Protein. Chemosensors, 2021, 9, 106.	3.6	8
2	Developing an Algorithm for Discriminating Oral Cancerous and Normal Tissues Using Raman Spectroscopy. Journal of Personalized Medicine, 2021, 11, 1165.	2.5	9
3	Annealing-Dependent Breakdown Voltage and Capacitance of Gallium Oxide-Based Gallium Nitride MOSOM Varactors. Materials, 2020, 13, 4956.	2.9	1
4	Novel Quantitative Analysis Using Optical Imaging (VELscope) and Spectroscopy (Raman) Techniques for Oral Cancer Detection. Cancers, 2020, 12, 3364.	3.7	9
5	Surface Acoustic Wave Sensor for C-Reactive Protein Detection. Sensors, 2020, 20, 6640.	3.8	17
6	The Improvement of Bonding Metal Layers in a GaAs Vertical Structure Light-Emitting Diode Package. Journal of Electronic Materials, 2020, 49, 6859-6864.	2.2	1
7	Effects of Annealing on Characteristics of Cu2ZnSnSe4/CH3NH3PbI3/ZnS/IZO Nanostructures for Enhanced Photovoltaic Solar Cells. Nanomaterials, 2020, 10, 521.	4.1	13
8	The Characteristics of Perovskite Solar Cells Fabricated Using DMF and DMSO/GBL Solvents. Journal of Electronic Materials, 2020, 49, 6823-6828.	2.2	13
9	Multiclass classification of autofluorescence images of oral cavity lesions based on quantitative analysis. PLoS ONE, 2020, 15, e0228132.	2.5	19
10	Capacitance Characteristics and Breakdown Mechanism of AlGaN/GaN Metalâ€“Semiconductorâ€“Metal Varactors and their Anti-Surge Application. Crystals, 2020, 10, 292.	2.2	2
11	GaN 2DEG Varactor-Based Impulse Suppression Module for Protection Against Malicious Electromagnetic Interference. Journal of Electronic Materials, 2020, 49, 6798-6805.	2.2	2
12	Raman Spectroscopy Analysis for Optical Diagnosis of Oral Cancer Detection. Journal of Clinical Medicine, 2019, 8, 1313.	2.4	65
13	Reactive Mechanism of Cu2ZnSnSe4 Thin Films Prepared by Reactive Annealing of the Cu/Zn Metal Layer in a SnSex + Se Atmosphere. Crystals, 2019, 9, 10.	2.2	14
14	Deep Etched Gallium Nitride Waveguide for Raman Spectroscopic Applications. Crystals, 2019, 9, 176.	2.2	2
15	Low-Cost CuIn1â^'xGaxSe2 Ultra-Thin Hole-Transporting Material Layer for Perovskite/CIGSe Heterojunction Solar Cells. Applied Sciences (Switzerland), 2019, 9, 719.	2.5	7
16	Meta-Learning Techniques to Analyze the Raman Data for Optical Diagnosis of Oral Cancer Detection. , 2019, , .		1
17	RGB-Stack Light Emitting Diode Modules with Transparent Glass Circuit Board and Oil Encapsulation. Materials, 2018, 11, 365.	2.9	2
18	Frequency dependent capacitance of metal semiconductor metal varactor diode and its tunable filter application. , 2018, , .		0

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19	Formation of Cl-Doped ZnO Thin Films by a Cathodic Electrodeposition for Use as a Window Layer in CIGS Solar Cells. Materials, 2018, 11, 953.	2.9	6
20	Deep traps in the ZnO nanorods/Si solar cells. Journal of Alloys and Compounds, 2017, 708, 247-254.	5.5	15
21	Lifetime of excess electrons in Cuâ€“Znâ€“Snâ€“Se powders. Semiconductors, 2017, 51, 18-22.	0.5	1
22	Phosphor-Free InGaN White Light Emitting Diodes Using Flip-Chip Technology. Materials, 2017, 10, 432.	2.9	9
23	Output Properties of Transparent Submount Packaged FlipChip Light-Emitting Diode Modules. Applied Sciences (Switzerland), 2016, 6, 179.	2.5	2
24	Effect of Sn Content in a CuSnZn Metal Precursor on Formation of MoSe2 Film during Selenization in Se+SnSe Vapor. Materials, 2016, 9, 241.	2.9	11
25	Thickness effect of IGZO layer in light-addressable potentiometric sensor. , 2016, , .		0
26	Effect of the chemical composition of Cuâ€“Inâ€“Gaâ€“Se layers on the photoconductivity and conversion efficiency of CdS/CIGSe solar cells. Semiconductors, 2016, 50, 1344-1351.	0.5	1
27	The formation of MoSe<inf>2</inf> films during selenization process in CZTSe solar cells. , 2016, , .		0
28	Enhance the protection capability of intentional electro magnetic interference with Zinc Oxide sintered gas discharge tube. , 2015, , .		1
29	Improving Efficiency of Multicrystalline Silicon and CIGS Solar Cells by Incorporating Metal Nanoparticles. Materials, 2015, 8, 6761-6771.	2.9	40
30	Si/ZnO nanorods/Ag/AZO structures as promising photovoltaic plasmonic cells. Journal of Applied Physics, 2015, 117, .	2.5	17
31	Improved surge protection of flip-chip gallium nitride-based HEMTs by metal-semiconductor-metal two-dimensional electron gas varactor. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, 021401.	1.2	2
32	Capacitance Swing and Capacitance Ratio of GaN-Based Metal-Semiconductor-Metal Two-Dimensional Electron Gas Varactor with Different Dielectric Films. Journal of Electrical Engineering and Technology, 2015, 10, 1720-1725.	2.0	3
33	CZTSe solar cells prepared by electrodeposition of Cu/Sn/Zn stack layer followed by selenization at low Se pressure. Nanoscale Research Letters, 2014, 9, 678.	5.7	23
34	Tin sulfide thin films prepared by thermal evaporation and sulfurization. , 2014, , .		3
35	Bump and Underfill Effects on Thermal Behaviors of Flip-Chip LED Packages: Measurement and Modeling. IEEE Transactions on Device and Materials Reliability, 2014, 14, 161-168.	2.0	25
36	Comparison of silicone and spin-on glass packaging materials for light-emitting diode encapsulation. Thin Solid Films, 2014, 570, 496-499.	1.8	6

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37	Anomalous Decrease of Off-State Drain Leakage Current in GaN/AlGaN HEMTs With Dual Optical Excitation. IEEE Electron Device Letters, 2014, 35, 820-822.	3.9	2
38	Highly sensitive palladium oxide thin film extended gate FETs as pH sensor. Sensors and Actuators B: Chemical, 2014, 205, 199-205.	7.8	122
39	Improving the reliability of eutectic bonding vertical power light-emitting diodes by a Mo buffer layer. Thin Solid Films, 2014, 570, 500-503.	1.8	4
40	Improvement of Surge Protection by Using an AlGaN/GaN-Based Metalâ€“Semiconductorâ€“Metal Two-Dimensional Electron Gas Varactor. Japanese Journal of Applied Physics, 2012, 51, 124201.	1.5	4
41	Heat sink performances of GaN/InGaN flip-chip light-emitting diodes fabricated on silicon and AlN submounts. Microelectronics Reliability, 2012, 52, 884-888.	1.7	19
42	Improvement of Surge Protection by Using an AlGaN/GaN-Based Metalâ€“Semiconductorâ€“Metal Two-Dimensional Electron Gas Varactor. Japanese Journal of Applied Physics, 2012, 51, 124201.	1.5	5
43	An observation of charge trapping phenomena in GaN/AlGaN/Gd<inf>2</inf>O<inf>3</inf> MOS schottky structure. , 2011, , .		0
44	Effect of Electron Leakage on Efficiency Droop in Wide-Well InGaN-Based Light-Emitting Diodes. Applied Physics Express, 2011, 4, 012106.	2.4	30
45	An observation of charge trapping phenomena in GaN/AlGaN/Gd2O3/Niâ€“Au structure. Applied Physics Letters, 2011, 98, .	3.3	14
46	Electrostatic Reliability Characteristics of GaN Flip-Chip Power Light-Emitting Diodes With Metalâ€“Oxideâ€“Silicon Submount. IEEE Transactions on Electron Devices, 2010, 57, 119-124.	3.0	11
47	Improvement of crystal quality of AlN grown on sapphire substrate by MOCVD. Crystal Research and Technology, 2010, 45, 703-706.	1.3	13
48	Fabrication and thermal analysis of flip-chip light-emitting diodes with different numbers of Au stub bumps. Microelectronics Reliability, 2010, 50, 683-687.	1.7	20
49	High-Efficiency InGaN-Based Yellow-Green Light-Emitting Diodes. Japanese Journal of Applied Physics, 2010, 49, 021004.	1.5	14
50	Effects of Growth Parameters on Surface-morphological, Structural, Electrical and Optical Properties of AZO Films by RF Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2009, 1201, 149.	0.1	0
51	Wideâ€band doubleâ€ring resonator with transmission zeros and resonances using high permittivity aluminum nitride substrate. Microwave and Optical Technology Letters, 2009, 51, 2878-2882.	1.4	1
52	Lane detection system based on software and hardware codesign. , 2009, , .		3
53	The reflectivity of Mo/Ag/Au ohmic contacts on p-type GaN for flip-chip light-emitting diode (FCLED) applications. Applied Surface Science, 2008, 254, 4479-4482.	6.1	6
54	Effects of Growth Parameters on Surface-morphological, Structural and Electrical Properties of Mo Films by RF Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2008, 1123, 18.	0.1	3

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55	Formation process of high reflective Niâ•Agâ•Au Ohmic contact for GaN flip-chip light-emitting diodes. Applied Physics Letters, 2007, 90, 163515.	3.3	33
56	The Reflectivity enhancement of Ni/Ag/(Ti or Mo)/Au Ohmic Contact for Flip-Chip Light-Emitting Diode Applications. , 2007, , .		0
57	Light Output Improvement of InGaN-Based Light-Emitting Diodes by Microchannel Structure. IEEE Photonics Technology Letters, 2007, 19, 1175-1177.	2.5	13